

Description

The DMG3415UQ-7 uses advanced trench technology to provide excellent $R_{DS(ON)}$, This device is suitable for use as a load switch or in PWM applications.

General Features

 V_{DS} = -18V, I_{D} = -6.5A

 $R_{DS(ON)} < 28m\Omega @ V_{GS}$ =-4.5V

Application

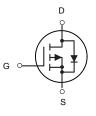
Battery protection

Load switch

Uninterruptible power supply







P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
DMG3415UQ-7	SOT-23	20P07	3000

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Limit	Unit
VDS	Drain-Source Voltage	-18	V
Vgs	Gate-Source Voltage	±12	V
ID	Drain Current-Continuous	-6.5	A
Іл	Drain Current-Pulsed (Note 1)	-15	A
PD	Maximum Power Dissipation	2	W
Тյ,Тѕтс	Operating Junction and Storage Temperature Range	-55 To 150	°C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	74	°C /W



P-Channel Enhancement Mode MOSFET

Electrical Characteristics (T_A=25°C unless otherwise noted)

Drain-Source Breakdown Voltage	BV _{DSS}	V_{GS} =0V I _D =-250µA	-	-18	-	V	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μA	
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±8V,V _{DS} =0V	-	-	±100	nA	
On Characteristics (Note 3)							
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =-250µA	-0.45	-0.7	-1.0	V	
Drain-Source On-State Resistance	P	V _{GS} =-4.5V, I _D =-4.1A	-	20	28		
	R _{DS(ON)}	V _{GS} =-2.5V, I _D =-3A	-	27	36	mΩ	
Forward Transconductance	g fs	V _{DS} =-5V,I _D =-3.5A	-	8.5	-	S	
Dynamic Characteristics (Note4)	·						
Input Capacitance	C _{lss}	$\gamma = 4\gamma \gamma = -0\gamma \gamma$	-	980	-	PF	
Output Capacitance	C _{oss}	– V _{DS} =-4V,V _{GS} =0V, – F=1.0MHz	-	450	-	PF	
Reverse Transfer Capacitance	C _{rss}	F = 1.010112	-	250	-	PF	
Switching Characteristics (Note 4)							
Turn-on Delay Time	t _{d(on)}		-	12	-	nS	
Turn-on Rise Time	tr	V _{DD} =-4V,I _D =-3.3A ,	-	35	-	nS	
Turn-Off Delay Time	t _{d(off)}	R_{L} =-1.2 Ω , V_{GEN} =-4.5 V , R_{g} =1 Ω	-	30	-	nS	
Turn-Off Fall Time	t _f		-	10	-	nS	
Total Gate Charge	Qg		-	7.8	-	nC	
Gate-Source Charge	Q _{gs}	V _{DS} =-4V,I _D =-4.1A,V _{GS} =-4.5V	-	1.2	-	nC	
Gate-Drain Charge	Q _{gd}		-	1.6	-	nC	
Drain-Source Diode Characteristics		•			-	·	
Diode Forward Voltage (Note 3)	V _{SD}	V _{GS} =0V,I _S =-1.6A	-	-	-1.2	V	
Diode Forward Current (Note 2)	I _S		-	-	1.6	А	

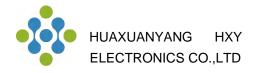
Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. Surface Mounted on FR4 Board, $t \le 10$ sec.

3. Pulse Test: Pulse Width \leq 300µs, Duty Cycle \leq 2%.

4. Guaranteed by design, not subject to production



DMG3415UQ-7 P-Channel Enhancement Mode MOSFET

Typical Characteristics

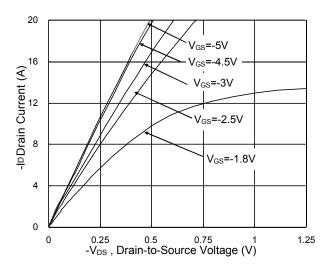


Fig.1 Typical Output Characteristics

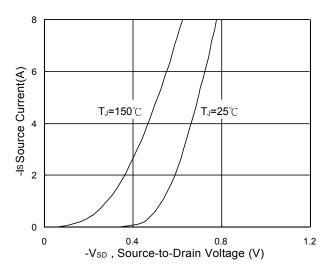


Fig.3 Forward Characteristics Of Reverse

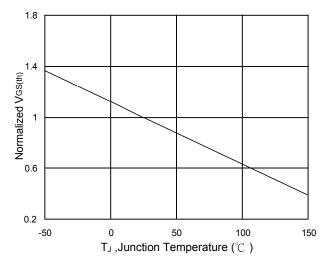


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

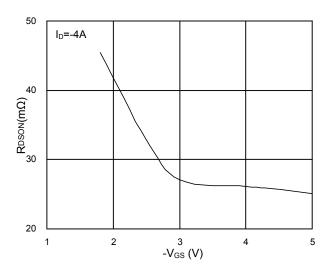


Fig.2 On-Resistance vs. Gate-Source

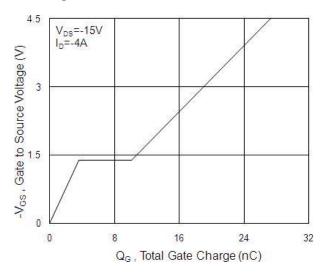


Fig.4 Gate-Charge Characteristics

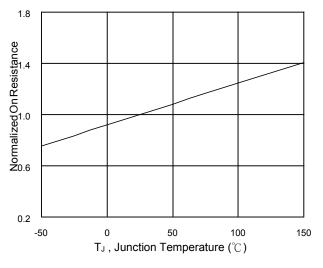
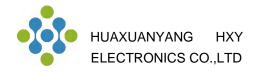


Fig.6 Normalized RDSON vs. TJ



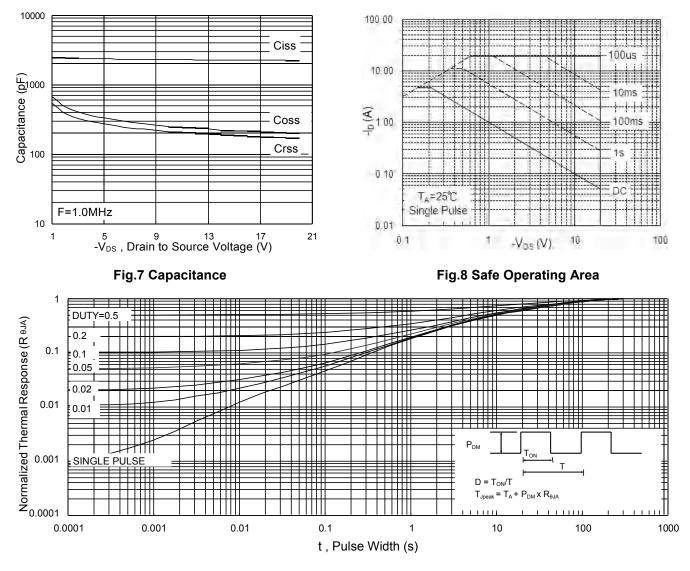


Fig.9 Normalized Maximum Transient Thermal Impedance

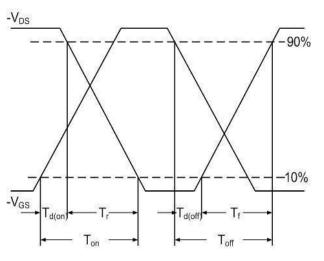


Fig.10 Switching Time Waveform

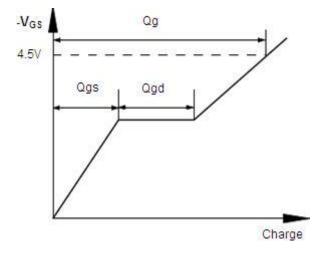
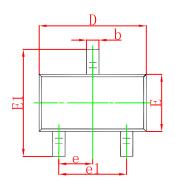
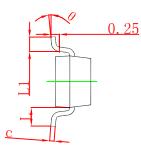


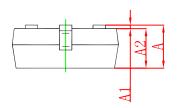
Fig.11 Gate Charge Waveform



SOT-23 Package Outline Dimensions

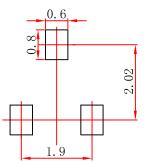






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



Note:

1.Controlling dimension: in millimeters.

2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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